

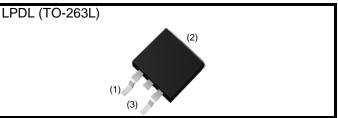
# **RGW40NL65HRBTL**

650V 20A Field Stop Trench IGBT

V <sub>CES</sub>	650V
Ι <sub>C</sub>	20A
V <sub>CE(sat) (Typ.)</sub>	1.5V
P <sub>D</sub>	144W

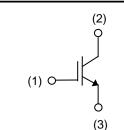
### ●Outline

Inner Circuit



### Features

- 1) AEC-Q101 Qualified
- 2) Low Collector Emitter Saturation Voltage
- 3) Low Switching Loss & Soft Switching
- 4) Pb free Lead Plating ; RoHS Compliant





### Packaging Specifications

	Packaging	Taping
	Reel Size (mm)	330
Type	Tape Width (mm)	24
Туре	Basic Ordering Unit (pcs)	1,000
	Packing Code	TL
	Marking	RGW40NL65

## Application

Automotive

On & Off Board Chargers

DC-DC Converters

PFC

Industrial Inverter

### • Absolute Maximum Ratings (at $T_c = 25^{\circ}C$ unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V <sub>CES</sub>	650	V
Gate - Emitter Voltage		V <sub>GES</sub>	±30	V
Collector Current	$T_{\rm C} = 25^{\circ}{\rm C}$	Ι <sub>C</sub>	48	А
	$T_{\rm C} = 100^{\circ}{\rm C}$	Ι <sub>C</sub>	30	А
Pulsed Collector Current		I <sub>CP</sub> *1	80	А
Power Dissipation	$T_{C} = 25^{\circ}C$	P <sub>D</sub>	144	W
	$T_{\rm C} = 100^{\circ}{\rm C}$	P <sub>D</sub>	72	W
Operating Junction Temperature		Tj	-40 to +175	°C
Storage Temperature		T <sub>stg</sub>	-55 to +175	°C

\*1 Pulse width limited by T<sub>jmax.</sub>

### •Thermal Resistance

Parameter	Symbol		Values		Unit
Falameter	Symbol	Min.	Тур.	Max.	Offic
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	1.04	°C/W

### ●IGBT Electrical Characteristics (at T<sub>i</sub> = 25°C unless otherwise specified)

Parameter	Symbol Conditions		Values			Unit
Farameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Collector - Emitter Breakdown Voltage	BV <sub>CES</sub>	$I_{\rm C}$ = 10µA, $V_{\rm GE}$ = 0V	650	-	-	V
Collector Cut - off Current	I <sub>CES</sub>	$V_{CE} = 650V, V_{GE} = 0V$	-	-	10	μA
Gate - Emitter Leakage Current	I <sub>GES</sub>	$V_{GE} = \pm 30V, V_{CE} = 0V$	-	-	±200	nA
Gate - Emitter Threshold Voltage	$V_{\text{GE(th)}}$	V <sub>CE</sub> = 5V, I <sub>C</sub> = 13.3mA	5.0	6.0	7.0	V
Collector - Emitter Saturation Voltage	V <sub>CE(sat)</sub>	$I_{C} = 20A, V_{GE} = 15V,$ $T_{j} = 25^{\circ}C$ $T_{j} = 175^{\circ}C$	-	1.5 1.85	1.9 -	V

Deremeter	Symbol	Conditions	Values			Linit	
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Input Capacitance	C <sub>ies</sub>	V <sub>CE</sub> = 30V,	-	1680	-		
Output Capacitance	C <sub>oes</sub>	V <sub>GE</sub> = 0V,	-	47	-	pF	
Reverse transfer Capacitance	C <sub>res</sub>	f = 1MHz	-	31	-		
Total Gate Charge	$Q_g$	V <sub>CE</sub> = 400V,	-	59	-		
Gate - Emitter Charge	$Q_{ge}$	I <sub>C</sub> = 20A,	-	13	-	nC	
Gate - Collector Charge	$Q_{gc}$	V <sub>GE</sub> = 15V	-	23	-		
Turn - on Delay Time	t <sub>d(on)</sub>		-	33	-		
Rise Time	t <sub>r</sub>	$I_{C} = 10A, V_{CC} = 400V,$ $V_{GE} = 15V, R_{G} = 10\Omega,$	-	7	-	- ns	
Turn - off Delay Time	t <sub>d(off)</sub>	$T_i = 25^{\circ}C$	-	129	-		
Fall Time	t <sub>f</sub>	Inductive Load	-	32	-		
Turn - on Switching Loss	$E_{on}$	*E <sub>on</sub> include diode reverse recovery	-	0.11	-	mJ	
Turn - off Switching Loss	$E_{off}$		-	0.16	-	mJ	
Turn - on Delay Time	t <sub>d(on)</sub>		-	32	-		
Rise Time	t <sub>r</sub>	$I_{C} = 10A, V_{CC} = 400V,$ $V_{GE} = 15V, R_{G} = 10\Omega,$	-	7	-	ns	
Turn - off Delay Time	t <sub>d(off)</sub>	$T_i = 175^{\circ}C$	-	143	-		
Fall Time	t <sub>f</sub>	Inductive Load	-	48	-		
Turn - on Switching Loss	$E_{on}$	*E <sub>on</sub> include diode reverse recovery	-	0.12	-	~	
Turn - off Switching Loss	$E_{off}$		-	0.21	-	mJ	
Reverse Bias Safe Operating Area	RBSOA	$I_{C} = 80A, V_{CC} = 520V,$ $V_{P} = 650V, V_{GE} = 15V,$ $R_{G} = 100\Omega, T_{i} = 175^{\circ}C$	FU	LL SQUA	RE	-	

### ●IGBT Electrical Characteristics (at T<sub>i</sub> = 25°C unless otherwise specified)

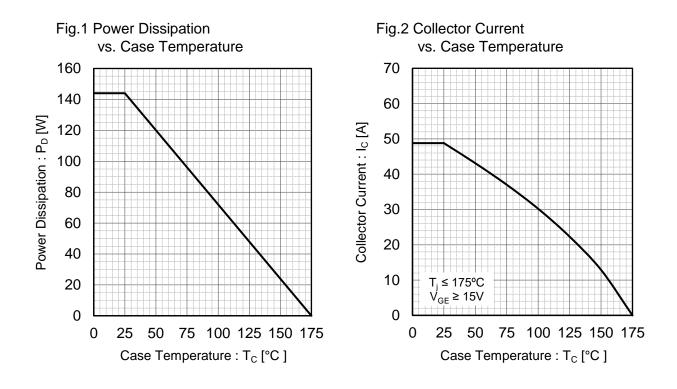
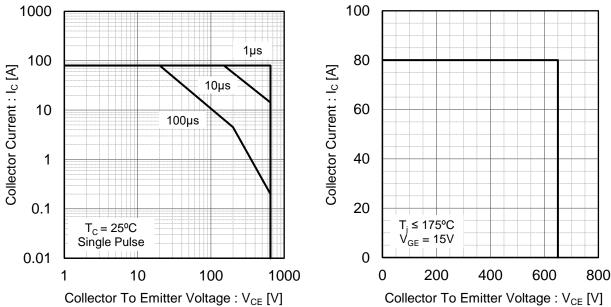


Fig.3 Forward Bias Safe Operating Area





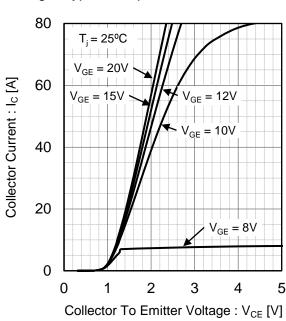


Fig.5 Typical Output Characteristics

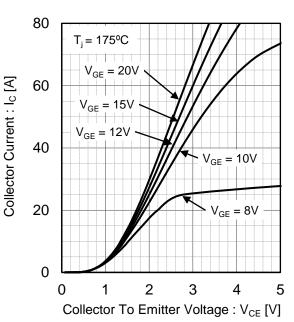
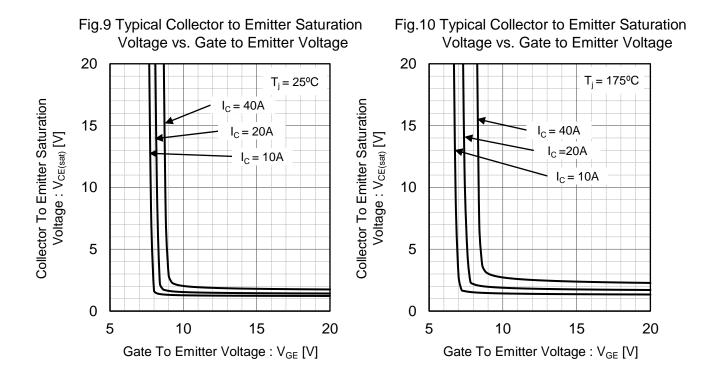
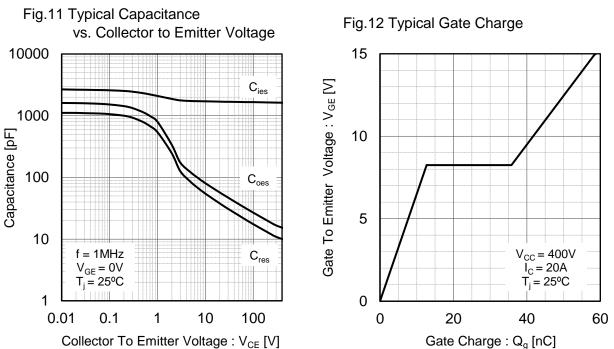


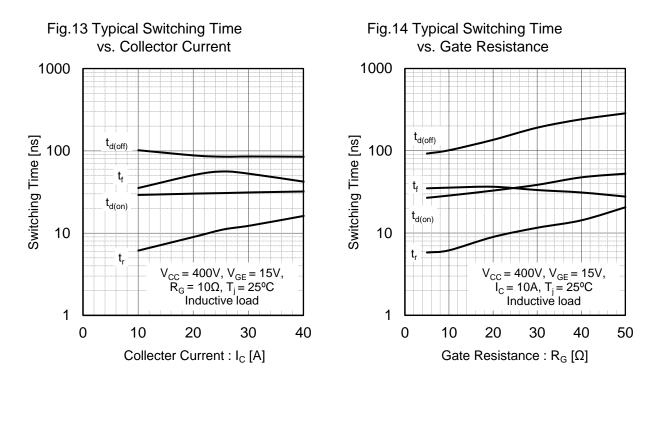
Fig.6 Typical Output Characteristics

Fig.8 Typical Collector to Emitter Saturation Fig.7 Typical Transfer Characteristics Voltage vs. Junction Temperature 4 40 V<sub>GE</sub> = 15V  $V_{CE} = 10V$ Collector To Emitter Saturation Collector Current : I<sub>c</sub> [A] 3 30 Voltage : V<sub>CE(sat)</sub> [V]  $I_{\rm C} = 40 {\rm A}$ 2 20  $I_{c} = 20A$  $I_{\rm C} = 10$ A 1 10 175°C T  $T_i = 25^{\circ}C$ 0 0 25 50 75 100 125 150 175 0 2 4 6 8 10 12 Gate To Emitter Voltage : V<sub>GE</sub> [V] Junction Temperature : T<sub>i</sub> [°C ]





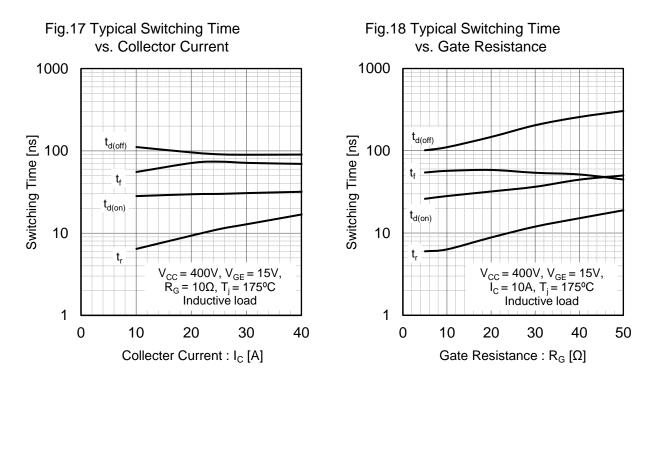
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### Fig.15 Typical Switching Energy Losses Fig.16 Typical Switching Energy Losses vs. Collector Current vs. Gate Resistance 10 10 Switching Energy Losses [mJ] Switching Energy Losses [mJ] 1 1 $\mathsf{E}_{\mathsf{off}}$ $\mathsf{E}_{\mathsf{off}}$ 0.1 0.1 $\mathsf{E}_{\mathsf{on}}$ Eon $V_{CC} = 400V, V_{GE} = 15V, R_{G} = 10\Omega, T_{j} = 25^{\circ}C$ $V_{CC} = 400V, V_{GE} = 15V,$ $I_{C} = 10A, T_{j} = 25^{\circ}C$ Inductive load Inductive load 0.01 0.01 0 10 20 30 40 0 10 20 30 Collecter Current : I<sub>C</sub> [A] Gate Resistance : $R_G [\Omega]$

40

50



### Fig.19 Typical Switching Energy Losses Fig.20 Typical Switching Energy Losses vs. Collector Current vs. Gate Resistance 10 10 Switching Energy Losses [mJ] Switching Energy Losses [mJ] 1 1 Eoff $\mathsf{E}_{\mathrm{off}}$ 0.1 0.1 $\mathsf{E}_{\mathsf{on}}$ Eon $V_{CC} = 400V, V_{GE} = 15V, R_{G} = 10\Omega, T_{j} = 175^{\circ}C$ V<sub>CC</sub> = 400V, V<sub>GE</sub> = 15V, I<sub>C</sub> = 10A, T<sub>j</sub> = 175°C Inductive load Inductive load 0.01 0.01 0 10 20 30 40 0 10 20 30 Collecter Current : I<sub>C</sub> [A] Gate Resistance : $R_G [\Omega]$

40

50

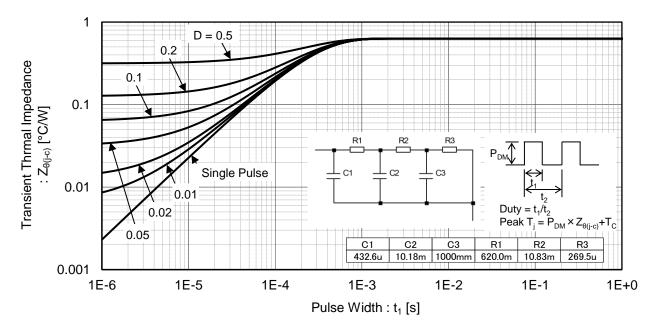


Fig.21 Typical IGBT Transient Thermal Impedance



### Inductive Load Switching Circuit and Waveform

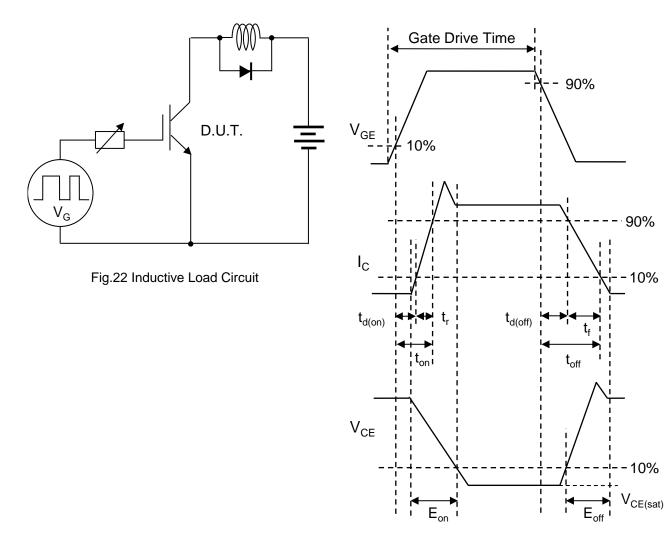


Fig.23 Inductive Load Waveform



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